SQ4401EY

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Vishay Siliconix

Automotive P-Channel 40 V (D-S) 175 °C MOSFET



| PRODUCT SUMMARY | | | | |
|---|--------|--|--|--|
| V _{DS} (V) | - 40 | | | |
| $R_{DS(on)}(\Omega)$ at V_{GS} = - 10 V | 0.014 | | | |
| $R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 V$ | 0.023 | | | |
| I _D (A) | - 17.3 | | | |
| Configuration | Single | | | |

FEATURES

- TrenchFET[®] Power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishav.com/doc?99912</u>

G

S

P-Channel MOSFET



ROHS COMPLIANT HALOGEN FREE

| ·D (• 9 | | |
|---------------------------------|--------|---|
| Configuration | Single | |
| ORDERING INFORMATION | | |
| Package | | SO-8 |
| Lead (Pb)-free and halogen-free | | SQ4401EY (for detailed order number please see <u>www.vishay.com/doc?79771</u>) |

| ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted) | | | | | |
|--|-------------------------|-----------------------------------|---------------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Drain-source voltage | | V _{DS} | - 40 | | |
| Gate-source voltage | | V _{GS} | ± 20 | V | |
| Orational during annual a | T _C = 25 °C | | - 17.3 | | |
| Continuous drain current ^a | T _C = 125 °C | ID ID | - 10 | | |
| Continuous source current (diode conduction) a | | I _S | - 6.5 | А | |
| Pulsed drain current ^b | | I _{DM} | - 69 | | |
| Single pulse avalanche current | L = 0.1 mH | I _{AS} | - 30 | | |
| Single pulse avalanche energy | L = 0.1 MH | E _{AS} | 45 | mJ | |
| Maximum power dissipation ^b | T _C = 25 °C | T _C = 25 °C | 7.14 | w | |
| | T _C = 125 °C | P _D | 2.4 | vv | |
| Operating junction and storage temperature | e range | T _J , T _{stg} | - 55 to + 175 | °C | |

| THERMAL RESISTANCE RATINGS | | | | | |
|----------------------------|------------------------|-------------------|-------|------|--|
| PARAMETER | | SYMBOL | LIMIT | UNIT | |
| Junction-to-ambient | PCB mount ^c | R _{thJA} | 85 | °C/W | |
| Junction-to-foot (drain) | | R _{thJF} | 21 | 0/10 | |

Notes

a. Package limited

b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%$

c. When mounted on 1" square PCB (FR-4 material)

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| PARAMETER | SYMBOL | TES | MIN. | TYP. | MAX. | UNIT | |
|---|--------------------------|--|--|-------|-------|-------|------|
| Static | | - | | | | | |
| Drain-source breakdown voltage | V _{DS} | V _{GS} = 0, I _D = - 250 μA | | - 40 | - | - | v |
| Gate-source threshold voltage | V _{GS(th)} | V _{DS} = | V _{GS} , I _D = - 250 μA | - 1.5 | - 2.0 | - 2.5 | v |
| Gate-source leakage | I _{GSS} | V _{DS} = | 0 V, $V_{GS} = \pm 20$ V | - | - | ± 100 | nA |
| | | $V_{GS} = 0 V$ | V _{DS} = - 40 V | - | - | - 1.0 | |
| Zero gate voltage drain current | I _{DSS} | $V_{GS} = 0 V$ | $V_{DS} = -40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$ | - | - | - 50 | μA |
| | | $V_{GS} = 0 V$ | $V_{DS} = -40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$ | - | - | - 150 | |
| On-state drain current ^a | I _{D(on)} | V _{GS} = - 10 V | $V_{DS} \ge -5 V$ | - 30 | - | - | Α |
| | | V _{GS} = - 10 V | I _D = - 10.5 A | - | 0.011 | 0.014 | Ω |
| Ducia composito en atata unaistanza a | B | V _{GS} = - 10 V | I _D = - 10.5 A, T _J = 125 °C | - | - | 0.020 | |
| Drain-source on-state resistance ^a | R _{DS(on)} | V _{GS} = - 10 V | I _D = - 10.5 A, T _J = 175 °C | - | - | 0.024 | |
| | | V _{GS} = - 4.5 V | l _D = - 8.7 A | - | 0.017 | 0.023 | |
| Forward transconductance ^a | 9 _{fs} | V _{DS} = - | - 15 V, I _D = - 10.5 A | - | 30 | - | S |
| Dynamic ^b | • | | | | | | |
| Input capacitance | C _{iss} | | 0 V V _{DS} = - 20 V, f = 1 MHz | - | 3400 | 4250 | pF |
| Output capacitance | C _{oss} | $V_{GS} = 0 V$ | | - | 440 | 550 | |
| Reverse transfer capacitance | C _{rss} | | | - | 350 | 436 | |
| Total gate charge ^c | Qg | | | - | 74 | 115 | |
| Gate-source charge ^c | Q _{gs} | V _{GS} = - 10 V | $V_{DS} = -20 V$, $I_{D} = -10.5 A$ | - | 11 | - | nC |
| Gate-drain charge ^c | Q _{gd} | | | - | 16 | - | |
| Gate resistance | R _g | | f = 1 MHz | | - | 3.21 | Ω |
| Turn-on delay time ^c | t _{d(on)} | | | - | 58 | 85 | |
| Rise time ^c | t _r | $\label{eq:VDD} \begin{array}{l} V_{\text{DD}} = -15 \ V, \ R_{\text{L}} = 15 \ \Omega \\ I_{\text{D}} \cong -1 \ A, \ V_{\text{GEN}} = -4.5 \ V, \ R_{\text{g}} = 6 \ \Omega \end{array}$ | | - | 76 | 105 | |
| Turn-off delay time ^c | t _{d(off)} | | | - | 67 | 85 | - ns |
| Fall time ^c | t _f | | | - | 44 | 55 | |
| Source-Drain Diode Ratings and Char | acteristics ^b | • | | | | | |
| Pulsed current ^a | I _{SM} | | | - | - | - 69 | Α |
| Forward voltage | V _{SD} | $I_{\rm F} = -2.7$ A, $V_{\rm GS} = 0$ | | - | - 0.8 | - 1.1 | V |

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

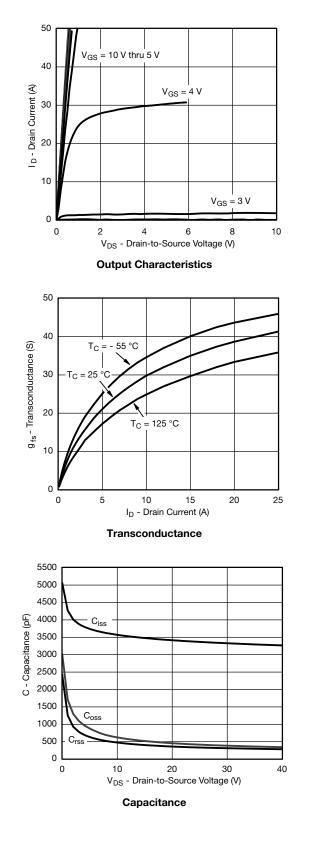
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

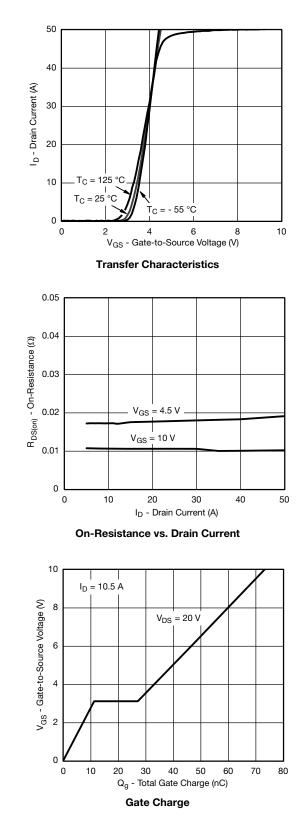
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TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)





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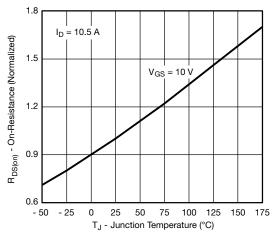
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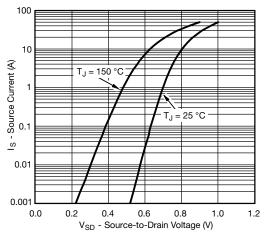
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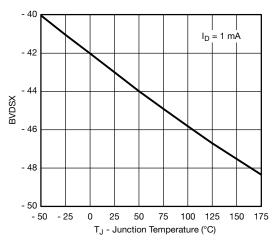
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



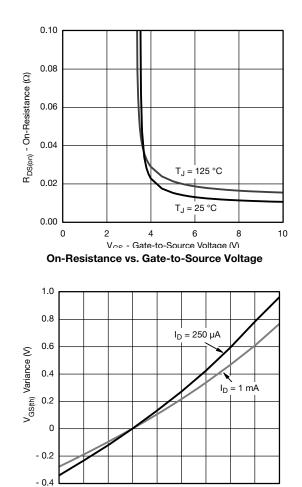
On-Resistance vs. Junction Temperature



Source Drain Diode Forward Voltage



Breakdown Voltage vs. Junction Temperature

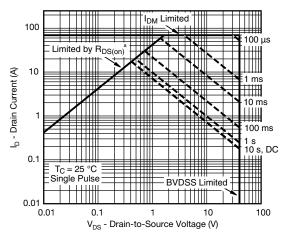


Threshold Voltage

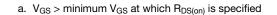
T_J - Temperature (°C)

25 50 75 100 125

- 50 - 25 0



Safe Operating Area



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Note

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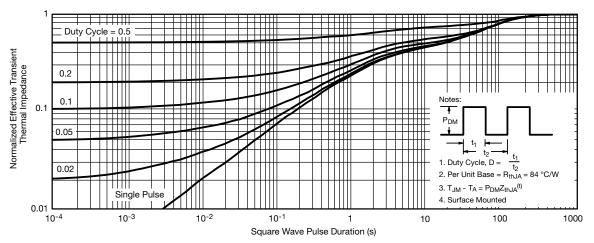
150 175

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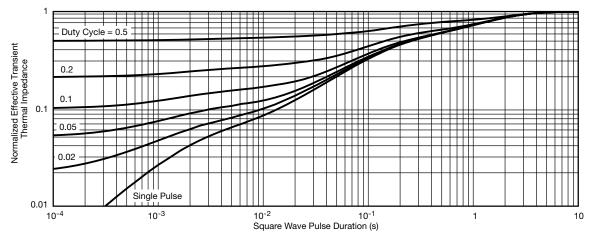


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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Foot (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?65901.

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Package Information

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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





| | MILLIMETERS | | INC | HES | |
|---|-------------|------|-----------|-------|--|
| DIM | Min | Мах | Min | Max | |
| A | 1.35 | 1.75 | 0.053 | 0.069 | |
| A ₁ | 0.10 | 0.20 | 0.004 | 0.008 | |
| В | 0.35 | 0.51 | 0.014 | 0.020 | |
| С | 0.19 | 0.25 | 0.0075 | 0.010 | |
| D | 4.80 | 5.00 | 0.189 | 0.196 | |
| E | 3.80 | 4.00 | 0.150 | 0.157 | |
| е | e 1.27 BSC | | 0.050 BSC | | |
| н | 5.80 | 6.20 | 0.228 | 0.244 | |
| h | 0.25 | 0.50 | 0.010 | 0.020 | |
| L | 0.50 | 0.93 | 0.020 | 0.037 | |
| q | 0° | 8° | 0° | 8° | |
| S | 0.44 | 0.64 | 0.018 | 0.026 | |
| ECN: C-06527-Rev. I, 11-Sep-06 DWG: 5498 | | | | | |

Application Note 826

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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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